

# MICROWAVE POWER GAAS FET

# TIM7179-30UL

#### MICROWAVE SEMICONDUCTOR TECHNICAL DATA

#### **FEATURES**

- ·BROAD BAND INTERNALLY MATCHED FET
- ·HIGH POWER

P1dB= 45.0dBm at 7.1GHz to 7.9GHz

·HIGH GAIN

G1dB= 8.5dB at 7.1GHz to 7.9GHz

**LOW INTERMODULATION DISTORTION** 

IM3(MIN.) = -44dBc at Pout= 34dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



# RF PERFORMANCE SPECIFICATIONS (Ta=25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 6.4A f= 7.1 to 7.9GHz  Two-Tone Test Po= 34dBm, Δf= 5MHz (Single Carrier Level)	dBm	44.0	45.0	_
Power Gain at 1dB Gain Compression Point	G1dB		dB	7.5	8.5	
Drain Current	IDS1		Α	_	7.0	8.0
Gain Flatness	ΔG		dB	_	_	±0.6
Power Added Efficiency	ηadd		%	_	39	_
3rd Order Intermodulation Distortion	IM3		dBc	-44	-47	_
Drain Current	IDS2		Α	_	7.0	8.0
Channel Temperature Rise	∆Tch	(VDS × IDS + Pin – P1dB) × Rth(c-c)	°C	_		100

Recommended Gate Resistance(Rg): 28 Ω

## **ELECTRICAL CHARACTERISTICS (Ta=25°C)**

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 10.0A	S	_	8.0	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 80mA	V	-0.5	-2.0	-3.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	Α	_	16.0	_
Gate-Source Breakdown Voltage	VGSO	IGS= -240μA	V	-5	_	_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		1.0	1.5

- MICROWAVE SEMICONDUCTOR TECHNICAL DATA

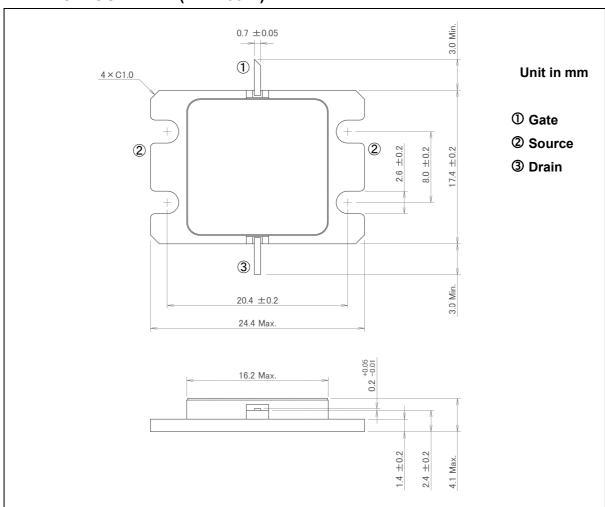
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# ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	18.0
Total Power Dissipation (Tc= 25°C)	PT	W	100
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

# PACKAGE OUTLINE (7-AA05A)



## HANDLING PRECAUTIONS FOR PACKAGE MODEL

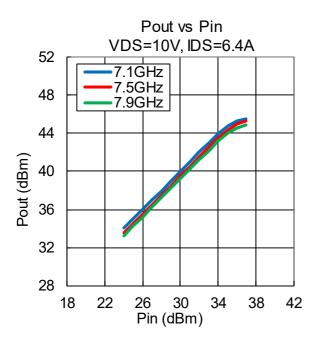
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3seconds at 350°C.

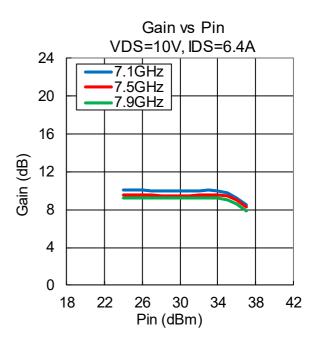


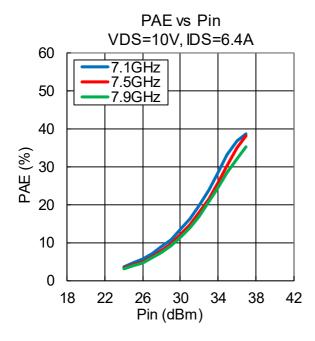
### TYPICAL RF PERFORMANCE

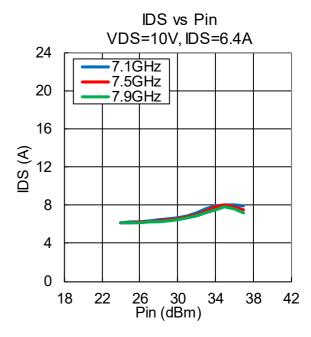
·Pout, Gain, PAE, IDS vs. Pin

VDS= 10 V, IDSset= 6.4 A, f= 7.1, 7.5, 7.9 GHz, Ta= +25 °C



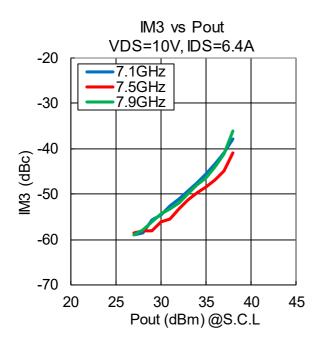


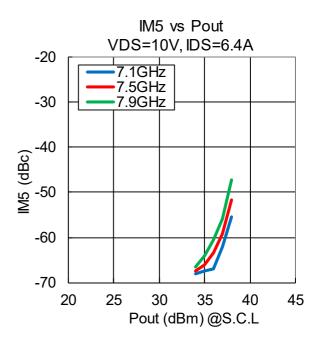




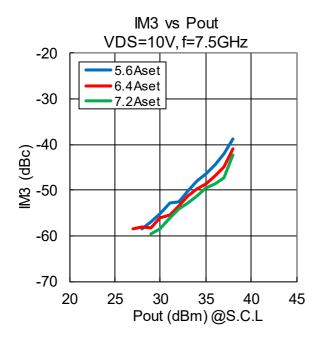
·IM3, IM5 vs. Pout

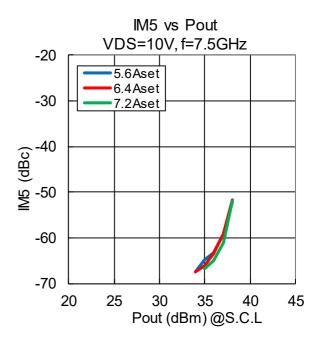
VDS= 10 V, IDSset= 6.4 A, f= 7.1, 7.5, 7.9 GHz,  $\Delta$ f= 5 MHz , Ta= +25  $^{\circ}$ C





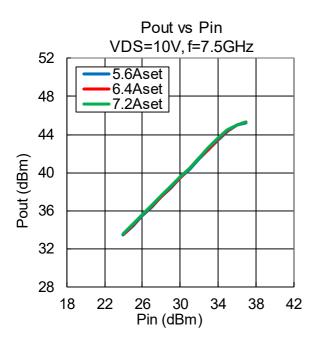
VDS= 10 V, IDSset= 5.6, 6.4, 7.2 A, f= 7. 5 GHz,  $\Delta$ f= 5 MHz , Ta= +25  $^{\circ}$ C

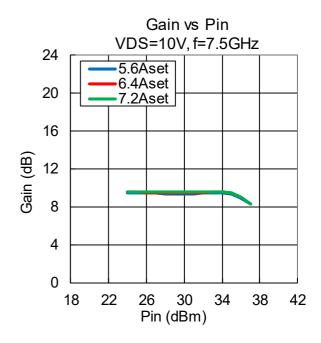


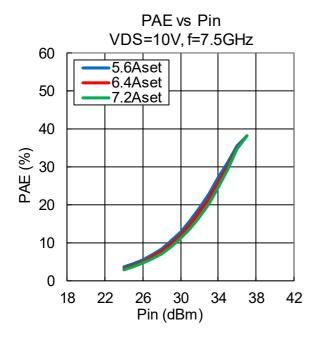


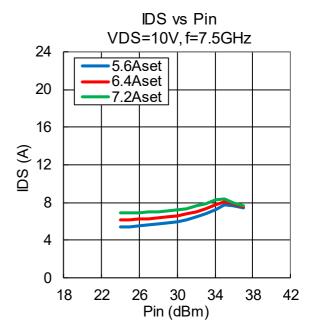
·Pout, Gain, PAE, IDS vs. Pin vs. IDSset

VDS= 10 V, IDSset= 5.6, 6.4, 7.2 A, f= 7.5 GHz, Ta= +25 °C





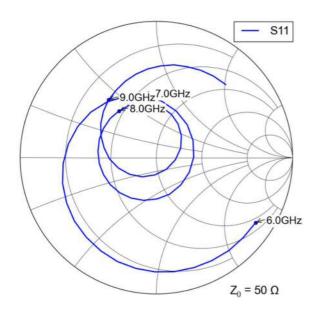


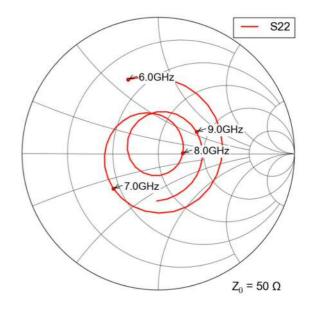


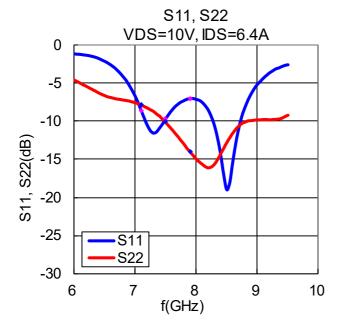


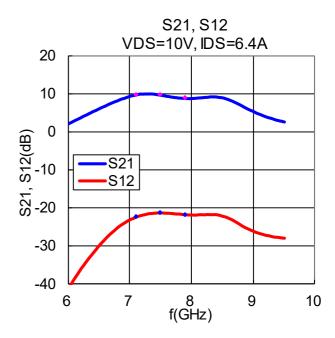
#### ·S-Parameters

VDS= 10 V, IDSset= 6.4 A, f= 6.0 to 9.5 GHz, Ta= +25  $^{\circ}$ C











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